

**Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>c</sub> = +25°C
-100V	83mΩ @ V <sub>GS</sub> = -10V	-20A
	89mΩ @ V <sub>GS</sub> = -6V	-19A

**Description and Applications**

This new generation Enhancement Mode MOSFET is designed to minimize R<sub>DS(ON)</sub> yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Active Clamp Switch
- Load Switch

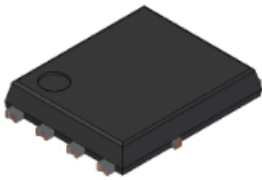
**Features and Benefits**

- 100% Unclamped Inductive Switch (UIS) Test in Production
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> – Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Wettable Flank for Improved Optical Inspections
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](https://www.diodes.com/quality/product-definitions/) or your local Diodes representative.**

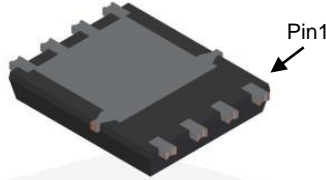
**Mechanical Data**

- Case: PowerDI<sup>®</sup>5060-8
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)

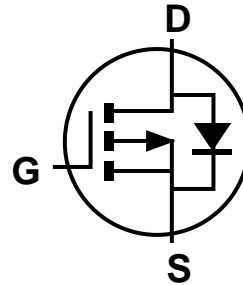
PowerDI5060-8 (SWP) (Type UX)



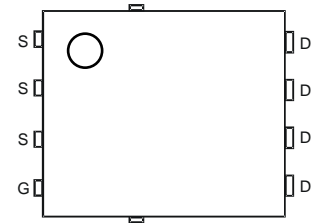
Top View



Bottom View



Internal Schematic



Top View  
Pin Configuration

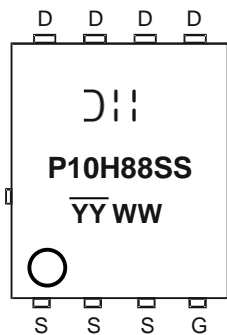
**Ordering Information** (Note 4)

Part Number	Case	Packaging
DMP10H088SPS-13	PowerDI5060-8 (SWP) (Type UX)	2,500 / Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

**Marking Information**

PowerDI5060-8 (SWP) (Type UX)



☺ = Manufacturer's Marking  
 P10H88SS = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Two Digits of Year (ex: 20 = 2020)  
 WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-100	V
Gate-Source Voltage			V <sub>GSS</sub>	±25	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = -10V	Steady State	T <sub>C</sub> = +25°C	I <sub>D</sub>	-20	A
		T <sub>C</sub> = +70°C		-15	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	-80	A
Maximum Continuous Body Diode Forward Current (Note 6)			I <sub>S</sub>	-20	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I <sub>SM</sub>	-80	A
Avalanche Current, L = 0.1mH			I <sub>AS</sub>	-32	A
Repetitive Avalanche Energy, L = 0.1mH			E <sub>AS</sub>	52	mJ

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	2.2	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	56	°C/W
Power Dissipation (Note 6)	P <sub>D</sub>	70	W
Thermal Resistance, Junction to Case (Note 6)	R <sub>θJC</sub>	1.8	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-100	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -1mA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1	µA	V <sub>DS</sub> = -80V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±25V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-2.0	—	-4.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	59	83	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -4.4A
		—	63	89		V <sub>GS</sub> = -6V, I <sub>D</sub> = -3.6A
Diode Forward Voltage	V <sub>SD</sub>	—	-0.7	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	1808	—	pF	V <sub>DS</sub> = -50V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	95	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	47	—	pF	
Gate Resistance	R <sub>g</sub>	—	10	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = -10V)	Q <sub>g</sub>	—	27.7	—	nC	V <sub>DS</sub> = -50V, I <sub>D</sub> = -4.4A
Total Gate Charge (V <sub>GS</sub> = -6V)	Q <sub>g</sub>	—	17.5	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	6.6	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	5.8	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	5.4	—	ns	V <sub>GS</sub> = -10V, V <sub>DS</sub> = -50V, R <sub>G</sub> = 6Ω, I <sub>D</sub> = -10A
Turn-On Rise Time	t <sub>r</sub>	—	17.4	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	38.6	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	88.6	—	ns	
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	29	—	ns	I <sub>F</sub> = -4.4A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	34	—	nC	I <sub>F</sub> = -4.4A, di/dt = 100A/µs

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  6. Thermal resistance from junction to soldering point (on the exposed drain pad).
  7. Short duration pulse test used to minimize self-heating effect.
  8. Guaranteed by design. Not subject to product testing.

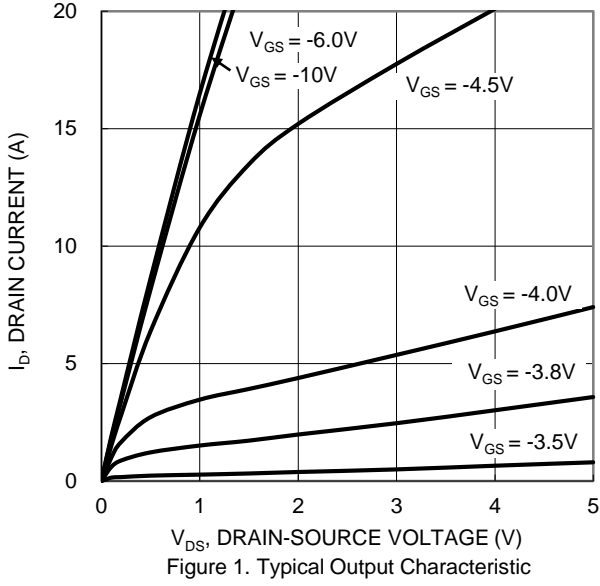


Figure 1. Typical Output Characteristic

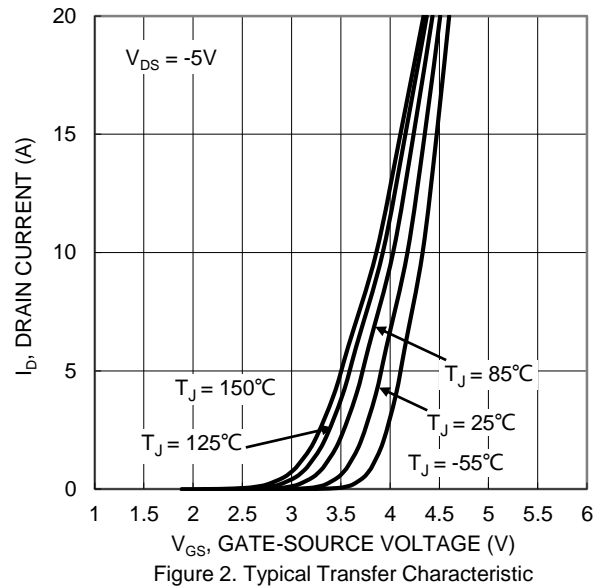


Figure 2. Typical Transfer Characteristic

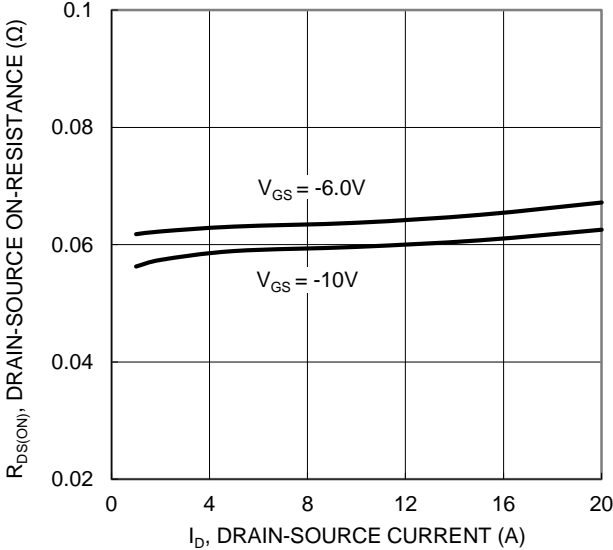


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

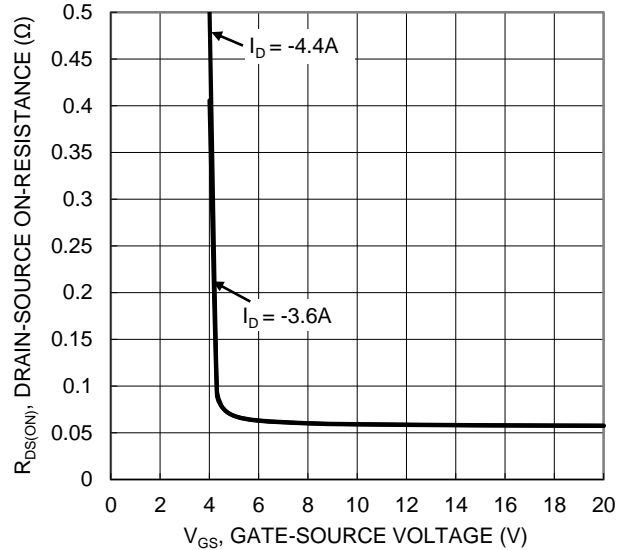


Figure 4. Typical Transfer Characteristic

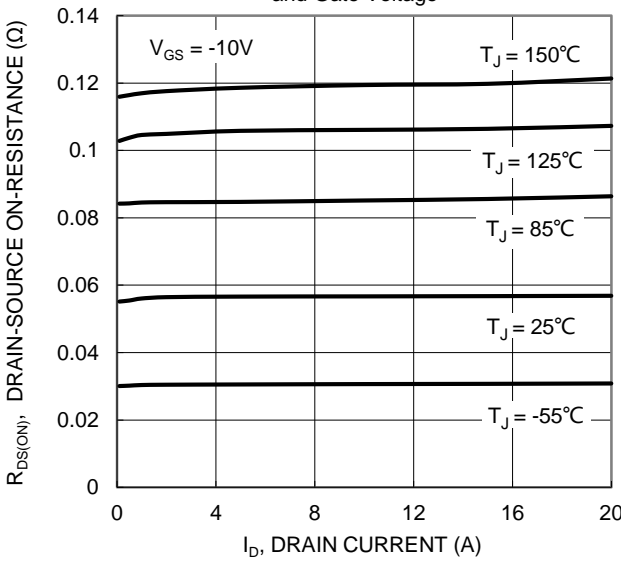


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

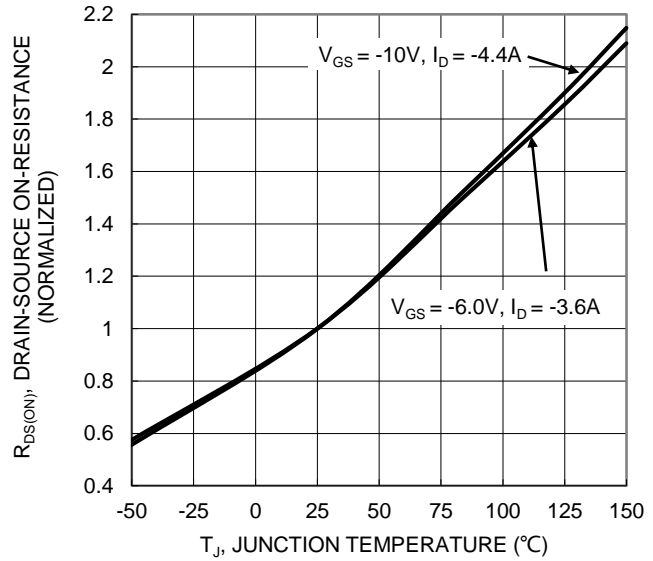
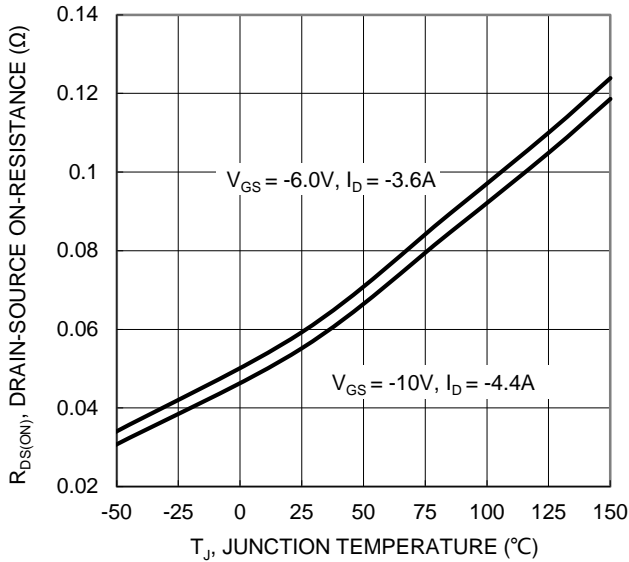
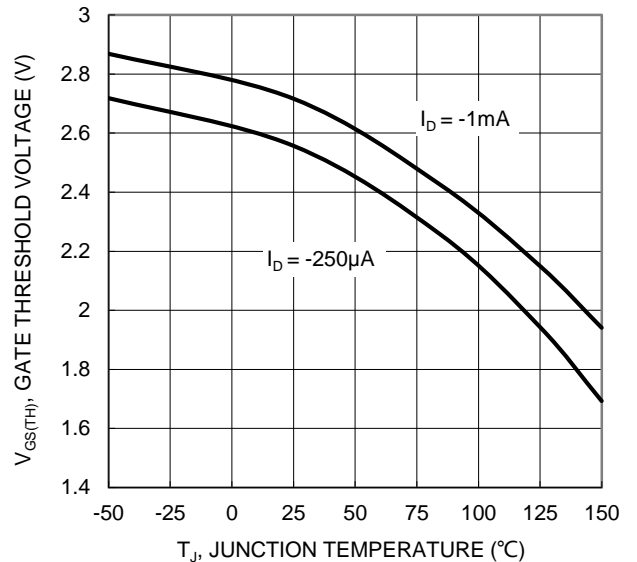


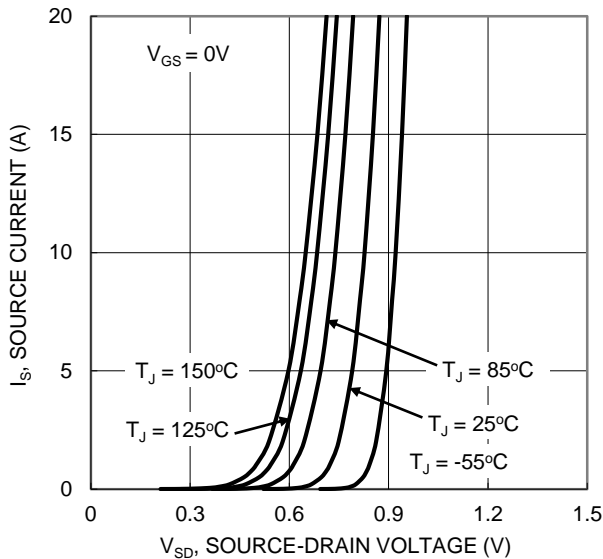
Figure 6. On-Resistance Variation with Junction Temperature



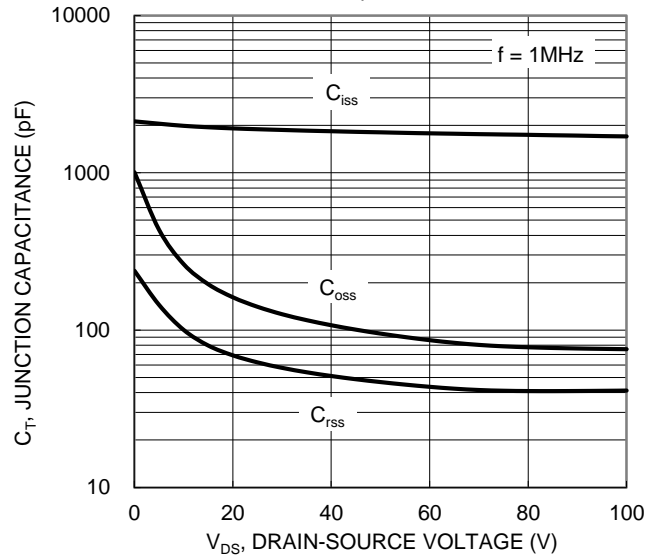
T<sub>J</sub>, JUNCTION TEMPERATURE (°C)  
Figure 7. On-Resistance Variation with Junction Temperature



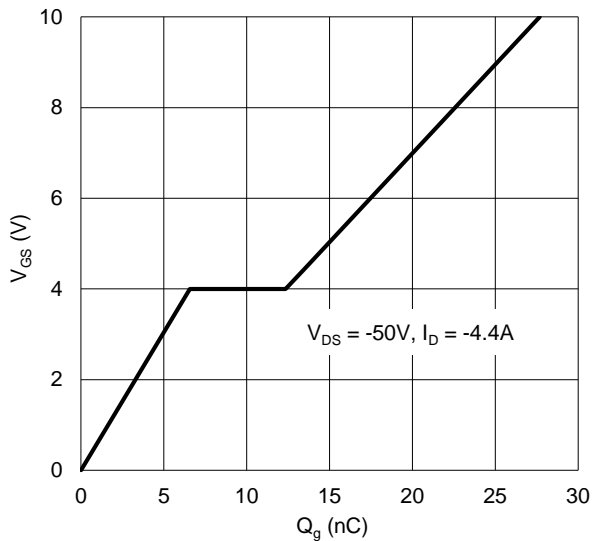
T<sub>J</sub>, JUNCTION TEMPERATURE (°C)  
Figure 8. Gate Threshold Variation vs. Junction Temperature



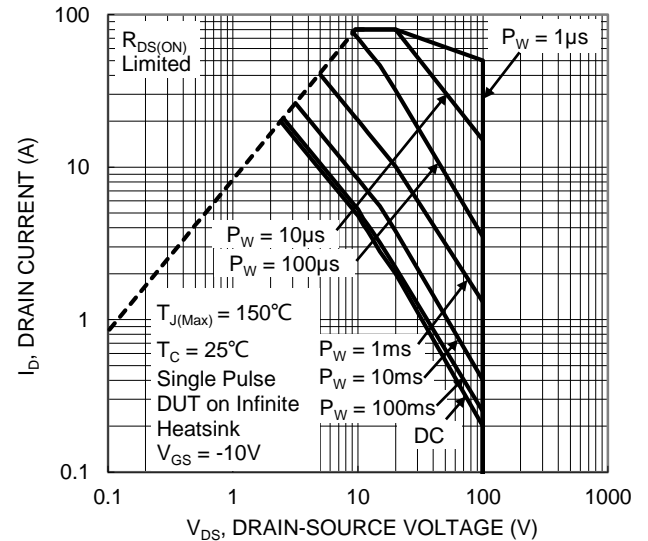
V<sub>SD</sub>, SOURCE-DRAIN VOLTAGE (V)  
Figure 9. Diode Forward Voltage vs. Current



V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V)  
Figure 10. Typical Junction Capacitance



Q<sub>g</sub> (nC)  
Figure 11. Gate Charge



V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V)  
Figure 12. SOA, Safe Operation Area

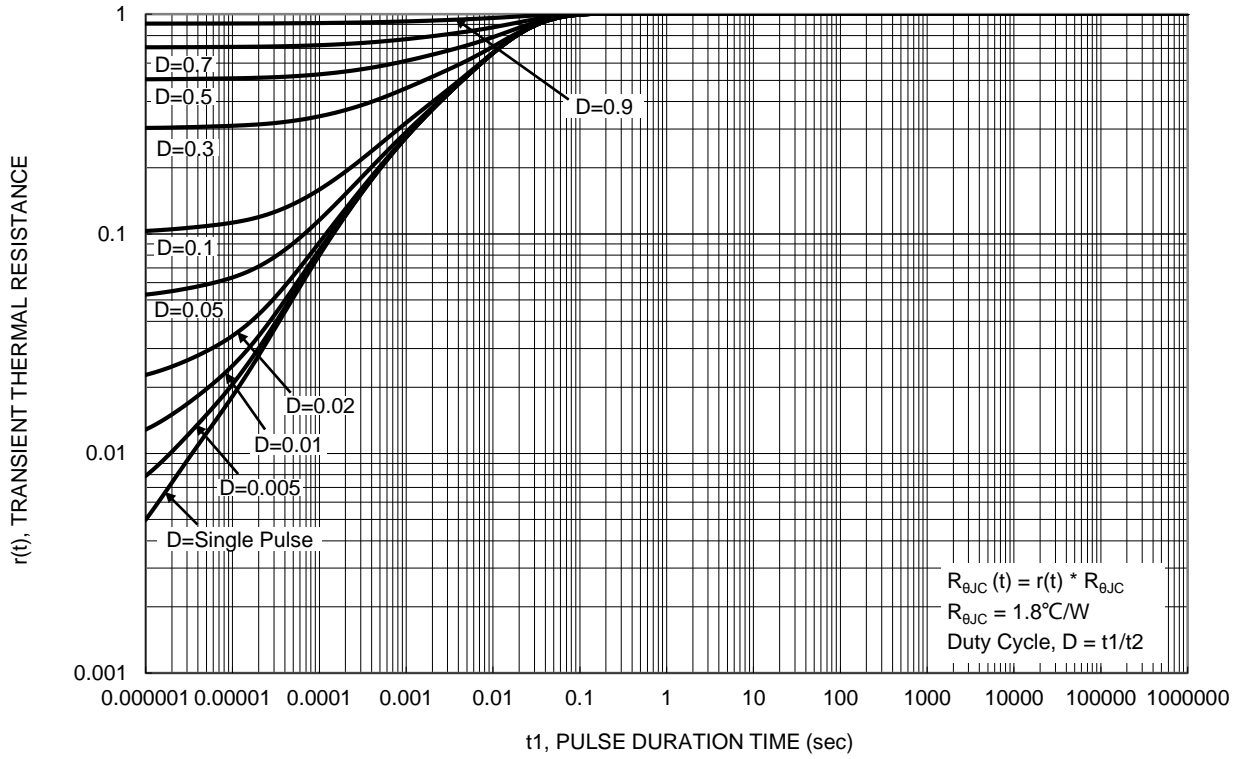
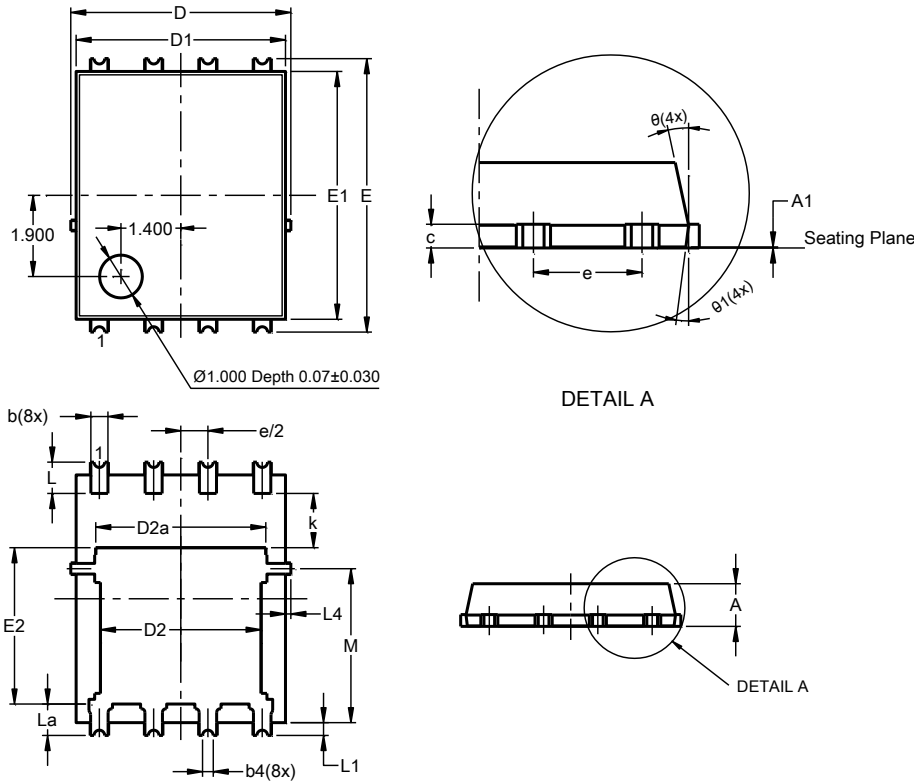


Figure 13. Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI5060-8 (SWP) (Type UX)**

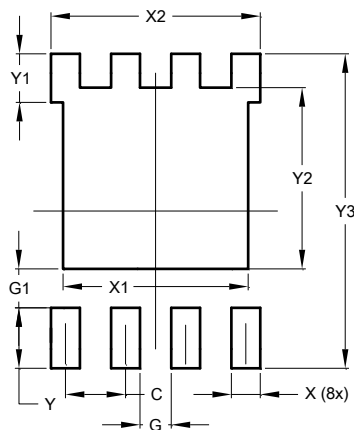


PowerDI5060-8 (SWP) (Type UX)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L1a	0.050REF		
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
theta	10°	12°	11°
theta1	6°	8°	7°
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI5060-8 (SWP) (Type UX)**



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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